

Peak gate current ($t_p=20 \text{ s}$, $T_j=125 \text{ }^\circ\text{C}$)

I_{GM}

4

ORDERING INFORMATION

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JieJie Microelectronics Co., Ltd.	Triacs	$I_{T(RMS)}:8A$	A:TO-220A(Ins)	800:V _{DRM} /V _{RRM} 1800V	TW:IGT1-3 05mA

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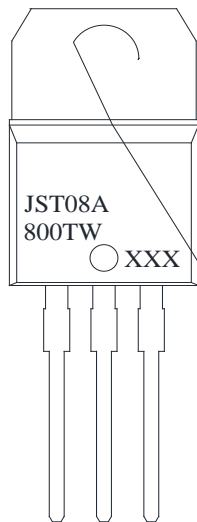


FIG.1: Maximum power dissipation versus RMS on-state current



FIG.2: RMS on-state current versus case temperature

v6W-



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